

BLF7G15LS-300P

Power LDMOS transistor

Rev. 3 — 12 July 2013

Product data sheet

1. Product profile

1.1 General description

300 W LDMOS power transistor for base station applications at frequencies from 1450 MHz to 1550 MHz.

Table 1. Typical performance

Typical RF performance at $T_{case} = 25\text{ °C}$ in a common source class-AB production test circuit.

Mode of operation	f (MHz)	I _{DQ} (mA)	V _{DS} (V)	P _{L(AV)} (W)	G _p (dB)	η _D (%)	ACPR (dBc)
2-carrier W-CDMA	1476 to 1511	2600	28	85	18	31	-32 [1]

[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 7.5 dB at 0.01 % probability on CCDF per carrier. Carrier spacing 5 MHz.

1.2 Features and benefits

- High efficiency
- Low R_{th} providing excellent thermal stability
- Designed for broadband operation (1450 MHz to 1550 MHz)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

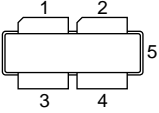
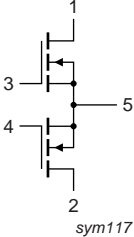
1.3 Applications

- RF power amplifiers for W-CDMA base stations and multi carrier applications in the 1450 MHz to 1550 MHz frequency range



2. Pinning information

Table 2. Discrete pinning

Pin	Description	Simplified outline	Graphic symbol
1	drain1		
2	drain2		
3	gate1		
4	gate2		
5	source		

[1] Connected to flange

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLF7G15LS-300P	-	earless flanged balanced LDMOST ceramic package; 4 leads	SOT539B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
I_D	drain current	per section	-	45	A
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 80\text{ °C}$; $P_L = 85\text{ W}$; $V_{DS} = 28\text{ V}$; $I_{Dq} = 2600\text{ mA}$	0.21	K/W

6. Characteristics

Table 6. Characteristics

$T_j = 25\text{ }^{\circ}\text{C}$; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}$; $I_D = 2.2\text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}$; $I_D = 220\text{ mA}$	1.5	1.9	2.3	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}$; $V_{DS} = 28\text{ V}$	-	-	2.8	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$; $V_{DS} = 10\text{ V}$	34	39	-	A
I_{GSS}	gate leakage current	$V_{GS} = 11\text{ V}$; $V_{DS} = 0\text{ V}$	-	-	280	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}$; $I_D = 11.0\text{ A}$	-	16.2	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V}$; $I_D = 7.7\text{ A}$	-	0.065	-	Ω

7. Test information

Table 7. Functional test information

Mode of operation: 2-carrier W-CDMA; PAR = 7.5 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 64 DPCH; $f_1 = 1473.5\text{ MHz}$; $f_2 = 1478.5\text{ MHz}$; $f_3 = 1508.5\text{ MHz}$; $f_4 = 1513.5\text{ MHz}$; RF performance at $V_{DS} = 28\text{ V}$; $I_{Dq} = 2600\text{ mA}$; $T_{case} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$P_{L(AV)}$	average output power		-	85	-	W
G_p	power gain	$P_{L(AV)} = 85\text{ W}$	17	18	-	dB
RL_{in}	input return loss	$P_{L(AV)} = 85\text{ W}$	-	-7	-6	dB
η_D	drain efficiency	$P_{L(AV)} = 85\text{ W}$	28	31	-	%
ACPR	adjacent channel power ratio	$P_{L(AV)} = 85\text{ W}$	-	-32	-28	dBc

Table 8. PAR performance

Mode of operation: 1-carrier W-CDMA; PAR = 7.5 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 64 DPCH; $f_1 = 1511\text{ MHz}$; RF performance at $V_{DS} = 28\text{ V}$; $I_{Dq} = 2600\text{ mA}$; $T_{case} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
PAR_O	output peak-to-average ratio	$P_{L(AV)} = 130\text{ W}$ at 0.01 % probability on CCDF	4.4	5.0	-	dB

7.1 Ruggedness in class-AB operation

The BLF7G15LS-300P is capable of withstanding a load mismatch corresponding to $V_{SWR} = 10 : 1$ through all phases under the following conditions: $V_{DS} = 28\text{ V}$; $I_{Dq} = 2600\text{ mA}$; $P_L = 100\text{ W (CW)}$; $f = 1450\text{ MHz to }1550\text{ MHz}$.

7.2 Impedance information

Table 9. Typical impedance per section (for the maximum peak power)
 $I_{Dq} = 1300\text{ mA}$; $V_{DS} = 28\text{ V}$.
 Z_S and Z_L defined in Figure 1.

f (MHz)	Z_S (Ω)	Z_L (Ω)
1410	$0.65 - j2.06$	$6.3 - j2.1$
1480	$0.55 - j1.92$	$7.2 - j1.3$
1560	$0.63 - j2.14$	$6.8 + j0.26$

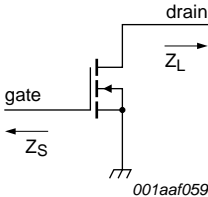
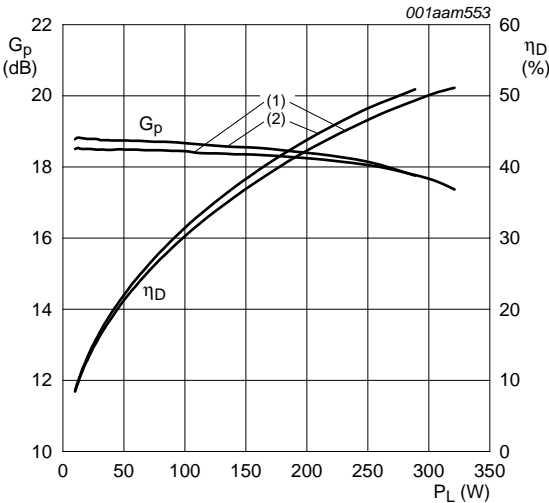


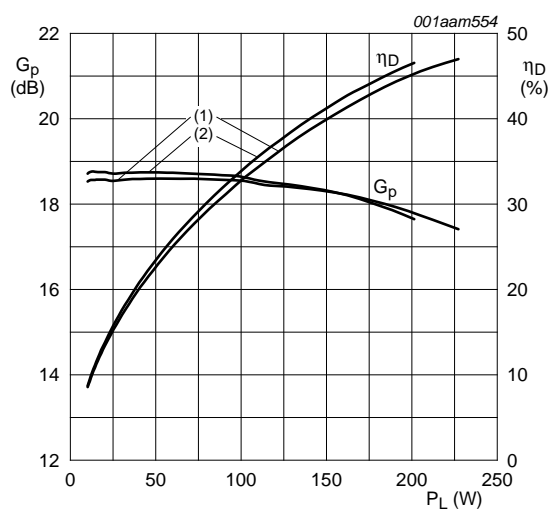
Fig 1. Definition of transistor impedance

7.3 Graphs



$V_{DS} = 28\text{ V}$; $I_{Dq} = 2600\text{ mA}$.
(1) $f = 1476\text{ MHz}$
(2) $f = 1511\text{ MHz}$

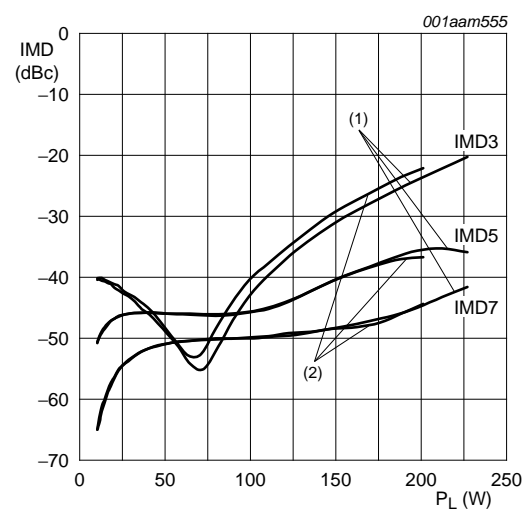
Fig 2. One-tone CW power gain and drain efficiency as function of load power; typical values



$V_{DS} = 28$ V; $I_{DQ} = 2600$ mA;
tone spacing 0.1 MHz.

- (1) $f = 1476$ MHz
- (2) $f = 1511$ MHz

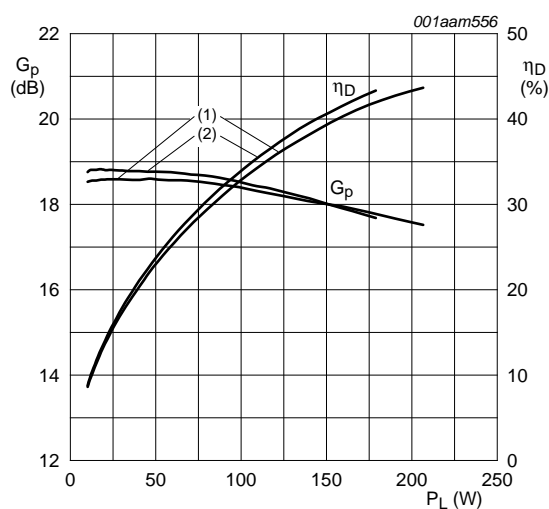
Fig 3. Two-tone CW power gain and drain efficiency as function of average load power; typical values



$V_{DS} = 28$ V; $I_{DQ} = 2600$ mA;
tone spacing 0.1 MHz.

- (1) $f = 1476$ MHz
- (2) $f = 1511$ MHz

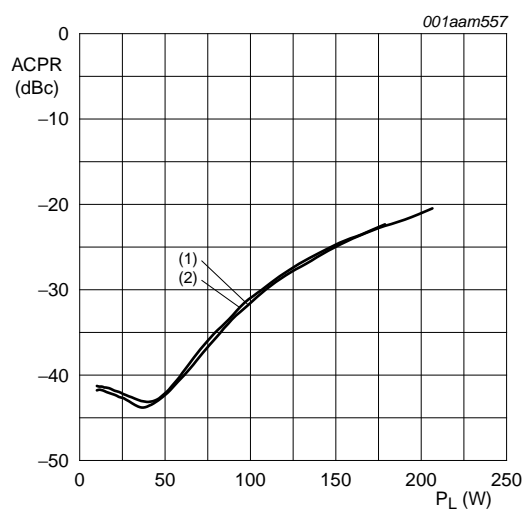
Fig 4. Two-tone intermodulation distortion as a function of average load power; typical values



$V_{DS} = 28$ V; $I_{DQ} = 2600$ mA;
carrier spacing 5 MHz.

- (1) $f = 1476$ MHz
- (2) $f = 1511$ MHz

Fig 5. 2-carrier W-CDMA power gain and drain efficiency as function of load power; typical values



$V_{DS} = 28$ V; $I_{DQ} = 2600$ mA;
carrier spacing 5 MHz.

- (1) $f = 1476$ MHz
- (2) $f = 1511$ MHz

Fig 6. 2-carrier W-CDMA adjacent channel power ratio as function of load power 5 MHz frequency offset; typical values

7.4 Test circuit

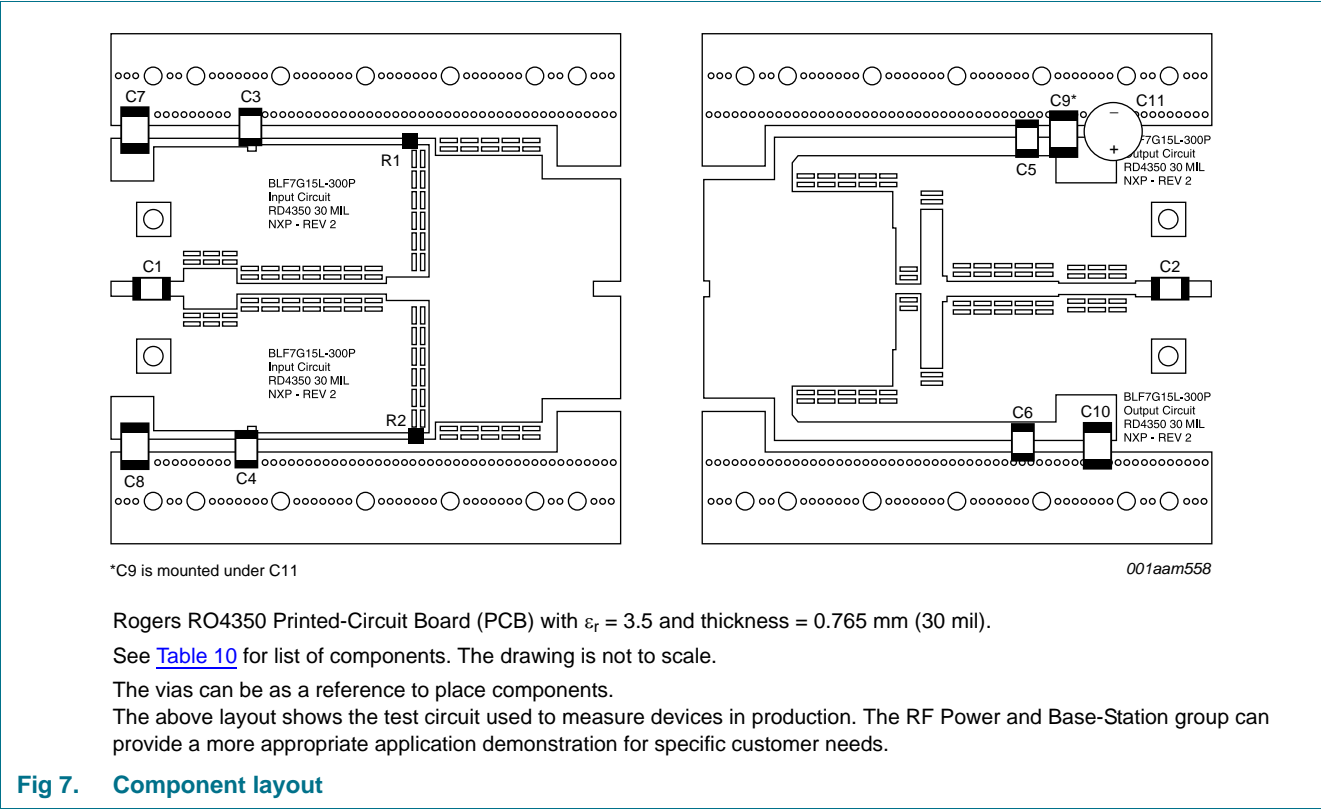


Table 10. List of components
See [Figure 7](#) for test circuit.

Component	Description	Value	Remarks
C1, C2	multi layer ceramic chip capacitor	100 pF	[1] ATC 800B
C3, C4	multi layer ceramic chip capacitor	68 pF	[1] ATC 800B
C5, C6	multi layer ceramic chip capacitor	47 pF	[1] ATC 800A
C7, C8, C9, C10	multi layer ceramic chip capacitor	10 μ F	Murata
C11	electrolytic capacitor	470 μ F; 63 V	
R1, R2	chip resistor	15 Ω	Philips 1206

[1] All ATC chip capacitors need to be soldered vertically.

9. Abbreviations

Table 11. Abbreviations

Acronym	Description
3GPP	Third Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LDMOST	Laterally Diffused Metal Oxide Semiconductor Transistor
PAR	Peak-to-Average power Ratio
RF	Radio Frequency
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

10. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF7G15LS-300P v.3	20130712	Product data sheet	-	BLF7G15LS-300P v.2
Modifications:	<ul style="list-style-type: none"> The package outline Figure 8 is updated. Translation disclaimer added to the legal text. 			
BLF7G15LS-300P v.2	20101203	Product data sheet	-	BLF7G15LS-300P v.1
Modifications:	<ul style="list-style-type: none"> Section 1.2 on page 1: list item "Excellent ruggedness" removed. Table 7 on page 3: values of RL_{in} have been projected on negative scale. Section "Handling information" removed 			
BLF7G15LS-300P v.1	20100921	Preliminary data sheet	-	-

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11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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13. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	2
6	Characteristics	3
7	Test information	3
7.1	Ruggedness in class-AB operation	3
7.2	Impedance information	4
7.3	Graphs	4
7.4	Test circuit	6
8	Package outline	7
9	Abbreviations	8
10	Revision history	8
11	Legal information	9
11.1	Data sheet status	9
11.2	Definitions	9
11.3	Disclaimers	9
11.4	Trademarks	10
12	Contact information	10
13	Contents	11

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